

Louise Lilja

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Wafer Scale On-Axis Homoepitaxial Growth of 4H-SiC(0001) for High-Power Devices: Influence of Different Gas Phase Chemistries and Growth Rate Limitations. <i>Crystal Growth and Design</i> , 2019, 19, 3288-3297.	1.4	7
2	In-grown stacking faults in 4H-SiC epilayers grown on 2° off-cut substrates. <i>Physica Status Solidi (B): Basic Research</i> , 2015, 252, 1319-1324.	0.7	4
3	Porous titania surfaces on titanium with hierarchical macro- and mesoporosities for enhancing cell adhesion, proliferation and mineralization. <i>Materials Science and Engineering C</i> , 2015, 47, 376-383.	3.8	25
4	Improved Epilayer Surface Morphology on 2° Off-Cut 4H-SiC Substrates. <i>Materials Science Forum</i> , 2014, 778-780, 206-209.	0.3	3
5	Oxidation Induced ON ₁ , ON _{2a/b} Defects in 4H-SiC Characterized by DLTS. <i>Materials Science Forum</i> , 2014, 778-780, 281-284.	0.3	2
6	Carrier Lifetime Controlling Defects $\langle i \rangle Z \langle /i \rangle$ and RB1 in Standard and Chlorinated Chemistry Grown 4H-SiC. <i>Crystal Growth and Design</i> , 2014, 14, 4104-4110.	1.4	14
7	The influence of growth conditions on carrier lifetime in 4H-SiC epilayers. <i>Journal of Crystal Growth</i> , 2013, 381, 43-50.	0.7	10
8	Influence of Growth Temperature on Carrier Lifetime in 4H-SiC Epilayers. <i>Materials Science Forum</i> , 2013, 740-742, 637-640.	0.3	4
9	Influence of Growth Mechanism on Carrier Lifetime in On-Axis Homoepitaxial Layers of 4H-SiC. <i>Materials Science Forum</i> , 2012, 717-720, 157-160.	0.3	1
10	Radial Variation of Measured Carrier Lifetimes in Epitaxial Layers Grown with Wafer Rotation. <i>Materials Science Forum</i> , 0, 717-720, 289-292.	0.3	1
11	The Effect of Growth Conditions on Carrier Lifetime in N-Type 4H-SiC Epitaxial Layers. <i>Materials Science Forum</i> , 0, 717-720, 161-164.	0.3	4
12	On-Axis Homoepitaxial Growth of 4H-SiC PiN Structure for High Power Applications. <i>Materials Science Forum</i> , 0, 740-742, 173-176.	0.3	3
13	Fast Growth Rate Epitaxy on 4° Off-Cut 4-Inch Diameter 4H-SiC Wafers. <i>Materials Science Forum</i> , 0, 778-780, 179-182.	0.3	6
14	Comparison of Carrier Lifetime Measurements and Mapping in 4H SiC Using Time Resolved Photoluminescence and $\langle i \rangle \frac{1}{4} \langle /i \rangle$ -PCD. <i>Materials Science Forum</i> , 0, 778-780, 301-304.	0.3	3
15	Smooth 4H-SiC Epilayers Grown with High Growth Rates with Silane/Propane Chemistry Using 4° Off-Cut Substrates. <i>Materials Science Forum</i> , 0, 858, 209-212.	0.3	2
16	Influence of n-Type Doping Levels on Carrier Lifetime in 4H-SiC Epitaxial Layers. <i>Materials Science Forum</i> , 0, 897, 238-241.	0.3	1